

SILICON NPN RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF260** is Designed for VHF Large Signal Power Amplifier Applications.

MAXIMUM RATINGS

I_C	1.0 A (CONT)
V_{CE}	18 V
P_{DISS}	12 W @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	14.6 °C/W

PACKAGE STYLE TO-220

	DIMENSIONS			
	mm		inches	
	min	max	min	max
A	10	10.4	0.393	0.409
B	15.2	15.9	0.598	0.626
C	12.7	13.7	0.500	0.539
D	6.2	6.6	0.244	0.260
E	4.4	4.6	0.173	0.181
F	3.5	5.5	0.137	0.216
G	2.65	2.95	0.104	0.116
H	17.6 typ.		0.692 typ.	
L	1.14	1.7	0.044	0.067
M	3.75	3.85	0.147	0.151
N	1.23	1.32	0.048	0.051
P	0.41	0.64	0.016	0.025
R	2.4	2.72	0.094	0.107
S	4.95	5.15	0.194	0.203
T	2.4	2.7	0.094	0.106
U	0.61	0.94	0.024	0.037

1 = BASE 2 = EMITTER 3 =
COLLECTOR MOUNTING TAB = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 10 mA	18			V
BV_{CES}	I _C = 5.0 mA	36			V
I_{CBO}	V _{CE} = 15 V			0.25	mA
I_{EBO}	V _{EB} = 4.0 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 250 mA	5.0			---
C_{ob}	V _{CB} = 15 V f = 1.0 MHz			20	pF
G_{PE}	V _{CC} = 12.5 V P _{out} = 5.0 W f = 175 MHz	10	11		dB
η		55			%